Voltage Regulator - Low Dropout, On/Off Control 300 mA

MC33375, NCV33375 Series

The MC33375 series are micropower low dropout voltage regulators available in a wide variety of output voltages as well as packages, SOT-223 and SOP-8. These devices feature a very low quiescent current and are capable of supplying output currents up to 300 mA. Internal current and thermal limiting protection are provided by the presence of a short circuit at the output and an internal thermal shutdown circuit.

The MC33375 has a control pin that allows a logic level signal to turn-off or turn-on the regulator output.

Due to the low input-to-output voltage differential and bias current specifications, these devices are ideally suited for battery powered computer, consumer, and industrial equipment where an extension of useful battery life is desirable.

Features:

- Low Quiescent Current (0.3 μA in OFF mode; 125 μA in ON mode)
- Low Input-to-Output Voltage Differential of 25 mV at I_O = 10 mA, and 260 mV at I_O = 300 mA
- Extremely Tight Line and Load Regulation
- Stable with Output Capacitance of only 0.33 μF for 2.5 V Output Voltage
- Internal Current and Thermal Limiting
- Logic Level ON/OFF Control
- NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable
- These are Pb-Free Devices

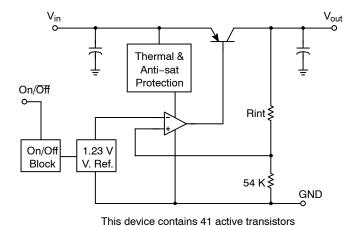


Figure 1. Simplified Block Diagram

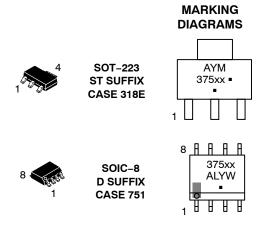
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LOW DROPOUT MICROPOWER VOLTAGE REGULATOR



A = Assembly Location

Y = Year

M = Date Code

L = Wafer Lot

W = Work Week

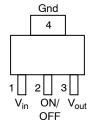
xx = Voltage Version= Pb-Free Package

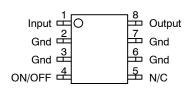
(Note: Microdot may be in either location)

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 11 of this data sheet.

PIN CONNECTIONS





MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Input Voltage	V _{CC}	13	Vdc
Power Dissipation and Thermal Characteristics $T_{\Delta} = 25^{\circ}\text{C}$			
Maximum Power Dissipation Case 751 (SOP-8) D Suffix	P _D	Internally Limited	W
Thermal Resistance, Junction-to-Ambient Thermal Resistance, Junction-to-Case Case 318E (SOT-223) ST Suffix	$egin{array}{l} R_{ hetaJA} \ R_{ hetaJC} \end{array}$	160 25	°C/W °C/W
Thermal Resistance, Junction-to-Air Thermal Resistance, Junction-to-Case	$egin{array}{l} R_{ hetaJA} \ R_{ hetaJC} \end{array}$	245 15	°C/W °C/W
Output Current	Io	300	mA
Maximum Junction Temperature	TJ	150	°C
Operating Ambient Temperature Range	T _A	- 40 to +125	°C
Storage Temperature Range	T _{stg}	– 65 to +150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

ELECTRICAL CHARACTERISTICS (C_L = 1.0 μ F, T_A = 25°C, for min/max values T_J = -40°C to +125°C, Note 1)

	Characteristic	Symbol	Min	Тур	Max	Unit
1.8 V Suffix 2.5 V Suffix 3.0 V Suffix 3.3 V Suffix 5.0 V Suffix	$I_{O} = 0$ mA to 250 mA $T_{A} = 25^{\circ}\text{C}$, $V_{in} = [V_{O} + 1] \text{ V}$	Vo	1.782 2.475 2.970 3.267 4.950	1.80 2.50 3.00 3.30 5.00	1.818 2.525 3.030 3.333 5.05	Vdc
1.8 V Suffix 2.5 V Suffix 3.0 V Suffix 3.3 V Suffix 5.0 V Suffix	$V_{in} = [V_O + 1] V, 0 < I_O < 100 \text{ mA}$ 2% Tolerance from $T_J = -40 \text{ to } +125^{\circ}\text{C}$		1.764 2.450 2.940 3.234 4.900	- - - -	1.836 2.550 3.060 3.366 5.100	
	V_{in} = [V_O + 1] V to 12 V, I_O = 250 mA, All Suffixes T_A = 25°C	Reg _{line}	-	2.0	10	mV
	Load Regulation $V_{in} = [V_O + 1] V$, $I_O = 0$ mA to 250 mA, All Suffixes $T_A = 25^{\circ}C$			5.0	25	mV
Dropout Voltage (N $I_O = 10 \text{ mA}$ $I_O = 100 \text{ mA}$ $I_O = 250 \text{ mA}$ $I_O = 300 \text{ mA}$	ote 3) T _J = -40°C to +125°C	V _{in} – V _O	- - -	25 115 220 260	100 200 400 500	mV
Ripple Rejection (1	20 Hz) V _{in(peak-peak)} = [V _O + 1.5] V to [V _O + 5.5] V	-	65	75	-	dB
'				160 46	- -	μVrms
CURRENT PARA	METERS					
Quiescent Current	ON Mode $V_{in} = [V_O + 1] V, I_O = 0 \text{ mA}$	I _{QOn}	-	125	200	μΑ
Quiescent Current	OFF Mode	I _{QOff}	-	0.3	4.0	μΑ
Quiescent Current ON Mode SAT $V_{in} = [V_O - 0.5] V$, $I_O = 0$ mA (Notes 2, 4) 3.0 V Suffix 3.3 V Suffix 5.0 V Suffix		I _{QSAT}	- - -	1500 1500 1500	2000 2000 2000	μΑ
Current Limit	I _{LIMIT}	-	450	-	mA	
ON/OFF INPUTS						
Logic "0" (Regula	e ator On) $V_{out} = V_O \pm 2\%$ ator Off) $V_{out} < 0.03 \text{ V}$ ator Off) $V_{out} < 0.05 \text{ V}$ (1.8 V Option)	V _{CTRL}	2.4 - -	- - -	- 0.5 0.3	V

Logic "0" (Regulator Off) V _{out} < 0.05 V (1.8 V Option)	0.3	
Logic "0" (Regulator Off) V _{out} < 0.03 V	0.5	

Thermal Shutdown

	Thermal Gradown			150	_	,
1	. Low duty pulse techniques are used during test to maintain junction temperatu	ure as close	to ambient a	s possible.		
	. Quiescent Current is measured where the PNP pass transistor is in saturation	$V_{in} = [V_O -$	- 0.5] V guar	antees this co	ondition.	

For 1.8 V version V_{DO} is constrained by the minimum input voltage of 2.5 V.
 For 1.8 V and 2.5 V versions, I_{QSAT} is constrained by the minimum input voltage of 2.5 V.

DEFINITIONS

Load Regulation – The change in output voltage for a change in load current at constant chip temperature.

Dropout Voltage – The input/output differential at which the regulator output no longer maintains regulation against further reductions in input voltage. Measured when the output drops 100 mV below its nominal value (which is measured at 1.0 V differential), dropout voltage is affected by junction temperature, load current and minimum input supply requirements.

Output Noise Voltage – The RMS AC voltage at the output with a constant load and no input ripple, measured over a specified frequency range.

Maximum Power Dissipation – The maximum total dissipation for which the regulator will operate within specifications.

Quiescent Current – Current which is used to operate the regulator chip and is not delivered to the load.

Line Regulation – The change in output voltage for a change in the input voltage. The measurement is made under conditions of low dissipation or by using pulse techniques such that the average chip temperature is not significantly affected.

Maximum Package Power Dissipation – The maximum package power dissipation is the power dissipation level at which the junction temperature reaches its maximum value i.e. 150° C. The junction temperature is rising while the difference between the input power ($V_{CC} \times I_{CC}$) and the output power ($V_{Out} \times I_{Out}$) is increasing.

Depending on ambient temperature, it is possible to calculate the maximum power dissipation and so the maximum current as following:

$$Pd = \frac{T_J - T_A}{R_{\theta JA}}$$

The maximum operating junction temperature T_J is specified at 150°C, if $T_A = 25$ °C, then P_D can be found. By neglecting the quiescent current, the maximum power dissipation can be expressed as:

$$I_{out} = \frac{P_D}{V_{CC} - V_{out}}$$

The thermal resistance of the whole circuit can be evaluated by deliberately activating the thermal shutdown of the circuit (by increasing the output current or raising the input voltage for example).

Then you can calculate the power dissipation by subtracting the output power from the input power. All variables are then well known: power dissipation, thermal shutdown temperature (150°C for MC33375) and ambient temperature.

$$R_{\theta JA} = \frac{T_J - T_A}{P_D}$$

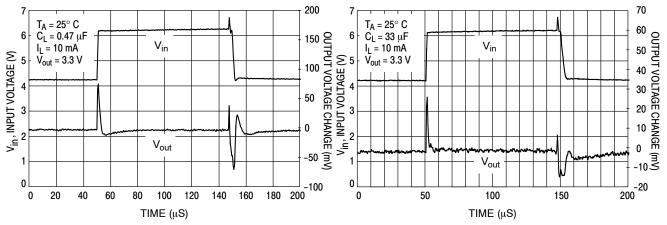


Figure 2. Line Transient Response

Figure 3. Line Transient Response

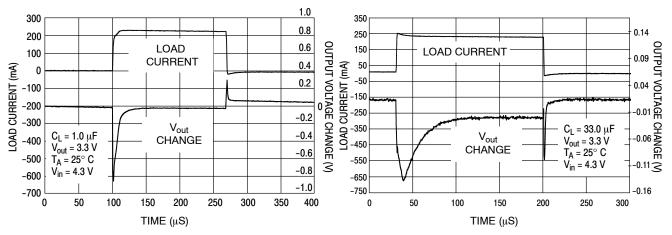


Figure 4. Load Transient Response

Figure 5. Load Transient Response

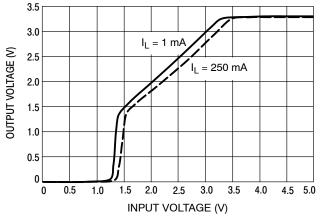


Figure 6. Output Voltage versus Input Voltage

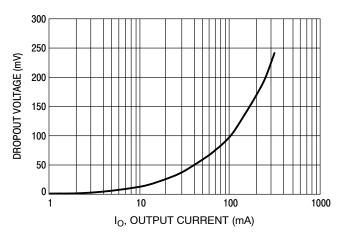


Figure 7. Dropout Voltage versus Output Current

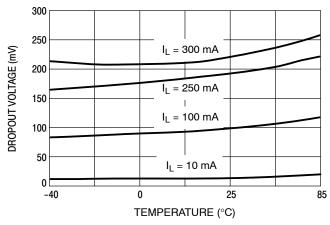


Figure 8. Dropout Voltage versus Temperature

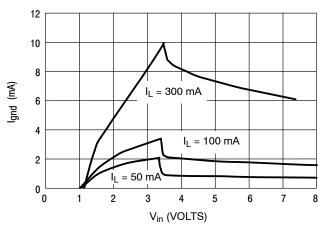


Figure 9. Ground Pin Current versus Input Voltage

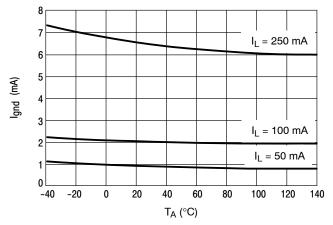


Figure 10. Ground Pin Current versus Ambient Temperature

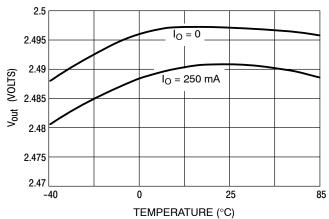


Figure 11. Output Voltage versus Ambient Temperature ($V_{in} = V_{out} + 1V$)

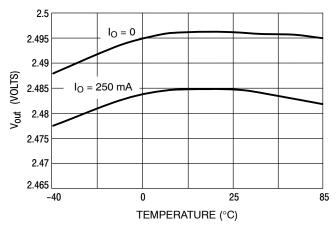


Figure 12. Output Voltage versus Ambient Temperature (V_{in} = 12 V)

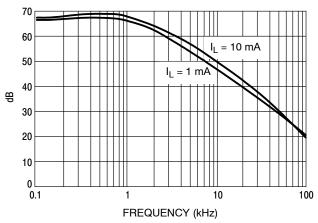


Figure 13. Ripple Rejection

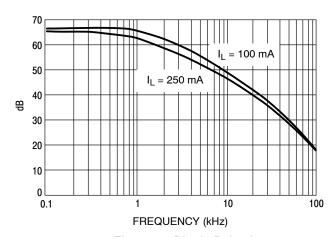


Figure 14. Ripple Rejection

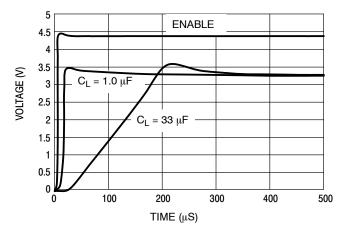


Figure 15. Enable Transient

1.8 V Option

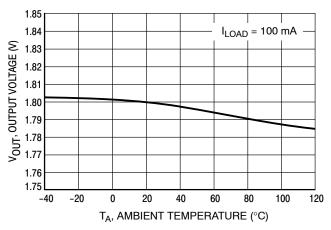


Figure 16. Output Voltage versus Temperature

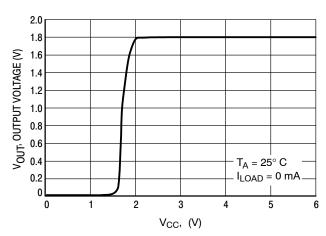


Figure 17. Output Voltage versus Input Voltage

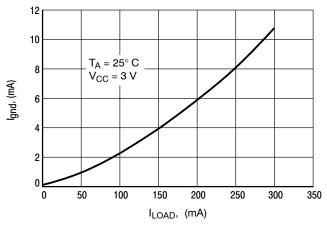


Figure 18. Ground Current versus Load Current

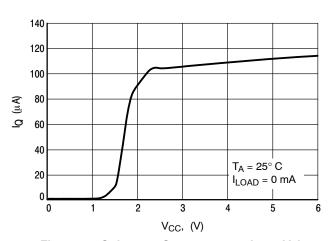


Figure 19. Quiescent Current versus Input Voltage

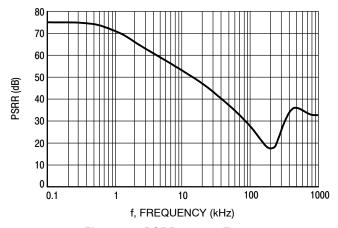


Figure 20. PSRR versus Frequency

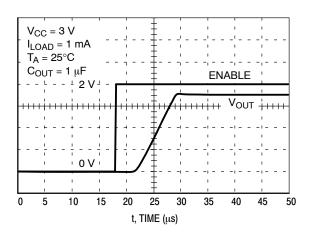


Figure 21. Enable Response

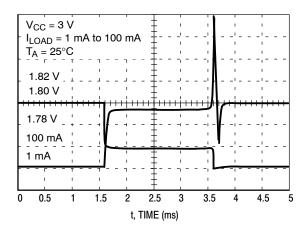


Figure 22. Load Transient Response

APPLICATIONS INFORMATION

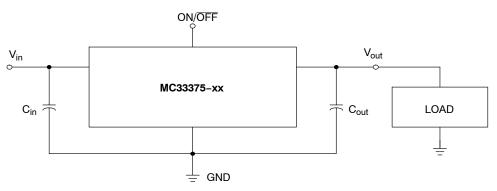


Figure 23. Typical Application Circuit

The MC33375 regulators are designed with internal current limiting and thermal shutdown making them user-friendly. Figure 15 is a typical application circuit. The output capability of the regulator is in excess of 300 mA, with a typical dropout voltage of less than 260 mV. Internal protective features include current and thermal limiting.

EXTERNAL CAPACITORS

These regulators require only a 0.33 µF (or greater) capacitance between the output and ground for stability for 1.8 V, 2.5 V, 3.0 V, and 3.3 V output voltage options. Output voltage options of 5.0 V require only 0.22 µF for stability. The output capacitor must be mounted as close as possible to the MC33375. If the output capacitor must be mounted further than two centimeters away from the MC33375, then a larger value of output capacitor may be required for stability. A value of 0.68 µF or larger is recommended. Most type of aluminum, tantalum, or multilayer ceramic will perform adequately. Solid tantalums or appropriate multilayer ceramic capacitors are recommended for operation below 25°C. An input bypass capacitor is recommended to improve transient response or if the regulator is connected to the supply input filter with long wire lengths, more than 4 inches. This will reduce the circuit's sensitivity to the input line impedance at high

frequencies. A 0.33 μF or larger tantalum, mylar, ceramic, or other capacitor having low internal impedance at high frequencies should be chosen. The bypass capacitor should be mounted with shortest possible lead or track length directly across the regulator's input terminals. Figure 16 shows the ESR that allows the LDO to remain stable for various load currents.

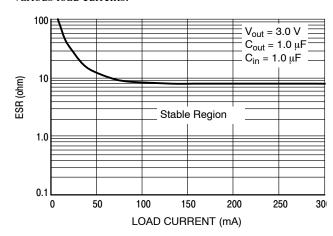


Figure 24. ESR for Vout = 3.0V

Applications should be tested over all operating conditions to insure stability.

THERMAL PROTECTION

Internal thermal limiting circuitry is provided to protect the integrated circuit in the event that the maximum junction temperature is exceeded. When activated, typically at 150°C, the output is disabled. There is no hysteresis built into the thermal protection. As a result the output will appear to be oscillating during thermal limit. The output will turn off until the temperature drops below the 150°C then the output turns on again. The process will repeat if the junction increases above the threshold. This will continue until the existing conditions allow the junction to operate below the temperature threshold.

Thermal limit is not a substitute for proper heatsinking.

The internal current limit will typically limit current to 450 mA. If during current limit the junction exceeds 150°C, the thermal protection will protect the device also. **Current limit is not a substitute for proper heatsinking.**

OUTPUT NOISE

In many applications it is desirable to reduce the noise present at the output. Reducing the regulator bandwidth by increasing the size of the output capacitor will reduce the noise on the MC33375.

ON/OFF PIN

When this pin is pulled low, the MC33375 is off. This pin should not be left floating. The pin should be pulled high for the MC33375 to operate.

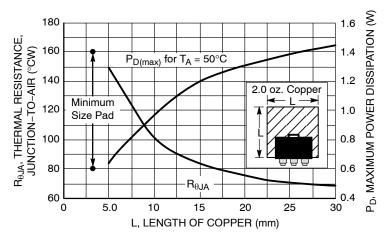


Figure 25. SOT–223 Thermal Resistance and Maximum Power Dissipation versus P.C.B. Copper Length

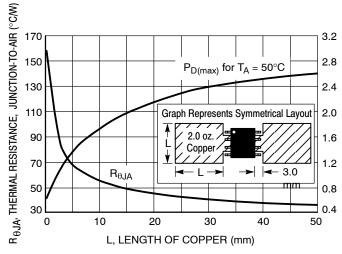


Figure 26. SOP-8 Thermal Resistance and Maximum Power Dissipation versus P.C.B. Copper Length

ORDERING INFORMATION

Device	Type	Operating Temperature Range, Tolerance	Package	Shipping †
MC33375ST-1.8T3G	1.8 V		SOT-223	
NCV33375ST1.8T3G*	(Fixed Voltage)		(Pb-Free)	4000 / Tape & Reel
MC33375D-2.5G			SOIC-8 (Pb-Free)	98 Units / Rail
MC33375D-2.5R2G	2.5 V		SOIC-8	
NCV33375D-2.5R2G*	(Fixed Voltage)		(Pb-Free)	2500 / Tape & Reel
MC33375ST-2.5T3G			SOT-223 (Pb-Free)	4000 / Tape & Reel
MC33375D-3.0G			SOIC-8 (Pb-Free)	98 Units / Rail
MC33375D-3.0R2G	3.0 V (Fixed Voltage)	1% Tolerance at T _A = 25°C	SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC33375ST-3.0T3G		2% Tolerance at T _J from -40 to +125°C	SOT-223 (Pb-Free)	4000 / Tape & Reel
MC33375D-3.3G			SOIC-8 (Pb-Free)	98 Units / Rail
MC33375D-3.3R2G	3.3 V		SOIC-8	
NCV33375D-3.3R2G*	(Fixed Voltage)		(Pb-Free)	2500 / Tape & Reel
MC33375ST-3.3T3G			SOT-223	
NCV33375ST3.3T3G*			(Pb-Free)	4000 / Tape & Reel
MC33375D-5.0G			SOIC-8 (Pb-Free)	98 Units / Rail
MC33375D-5.0R2G	5.0 V		SOIC-8 (Pb-Free)	2500 / Tape & Reel
NCV33375D-5.0R2G*	(Fixed Voltage)		SOIC-8 (Pb-Free)	2500 / Tape & Reel
MC33375ST-5.0T3G			SOT-223 (Pb-Free)	4000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

DEVICE MARKING

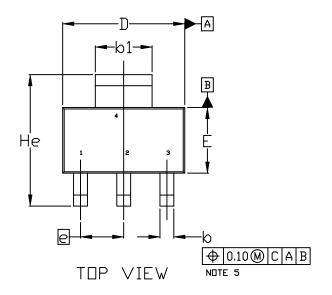
Device	Version	Marking (1st line)
MC33375, NCV33375	1.8 V	37518
MC33375, NCV33375	2.5 V	37525
MC33375	3.0 V	37530
MC33375, NCV33375	3.3 V	37533
MC33375, NCV33375	5.0 V	37550

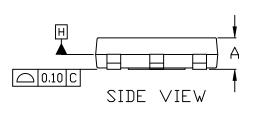
^{*}NCV Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q100 Qualified and PPAP Capable

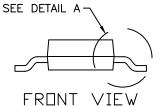


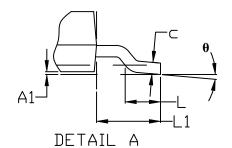
SOT-223 (TO-261) CASE 318E-04 ISSUE R

DATE 02 OCT 2018





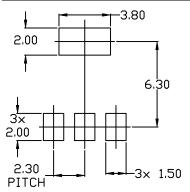




NOTES:

- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. DIMENSIONS D & E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
 MOLD FLASH, PROTRUSIONS OR GATE BURRS SHALL NOT EXCEED 0.200MM PER SIDE.
- 4. DATUMS A AND B ARE DETERMINED AT DATUM H.
- 5. ALLIS DEFINED AS THE VERTICAL DISTANCE FROM THE SEATING PLANE TO THE LOWEST POINT OF THE PACKAGE BODY.
- 6. POSITIONAL TOLERANCE APPLIES TO DIMENSIONS 6 AND 61.

	MILLIMETERS				
DIM	MIN.	MIN. N□M.			
Α	1.50	1.63	1.75		
A1	0.02	0.06	0.10		
b	0.60	0.75	0.89		
b1	2.90	3.06	3.20		
c	0.24	0.29	0.35		
D	6.30	6.50	6.70		
E	3.30	3.50	3.70		
е		5'30 B2C	,		
L	0.20				
L1	1.50	1.75	2.00		
He	6.70	7.00	7.30		
θ	0°		10°		



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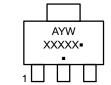
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DATE 02 OCT 2018

STYLE 1: PIN 1. BASE 2. COLLECTOR 3. EMITTER 4. COLLECTOR	STYLE 2: PIN 1. ANODE 2. CATHODE 3. NC 4. CATHODE	STYLE 3: PIN 1. GATE 2. DRAIN 3. SOURCE 4. DRAIN	STYLE 4: PIN 1. SOURCE 2. DRAIN 3. GATE 4. DRAIN	STYLE 5: PIN 1. DRAIN 2. GATE 3. SOURCE 4. GATE
STYLE 6: PIN 1. RETURN 2. INPUT 3. OUTPUT 4. INPUT	STYLE 7: PIN 1. ANODE 1 2. CATHODE 3. ANODE 2 4. CATHODE	STYLE 8: CANCELLED	STYLE 9: PIN 1. INPUT 2. GROUND 3. LOGIC 4. GROUND	STYLE 10: PIN 1. CATHODE 2. ANODE 3. GATE 4. ANODE
STYLE 11: PIN 1. MT 1 2. MT 2 3. GATE 4. MT 2	STYLE 12: PIN 1. INPUT 2. OUTPUT 3. NC 4. OUTPUT	STYLE 13: PIN 1. GATE 2. COLLECTOR 3. EMITTER 4. COLLECTOR		

GENERIC MARKING DIAGRAM*



A = Assembly Location

Y = Year W = Work Week

 $XXXXX \ = Specific \ Device \ Code$

= Pb-Free Package

(Note: Microdot may be in either location)
*This information is generic. Please refer to
device data sheet for actual part marking.
Pb-Free indicator, "G" or microdot "•", may
or may not be present. Some products may
not follow the Generic Marking.

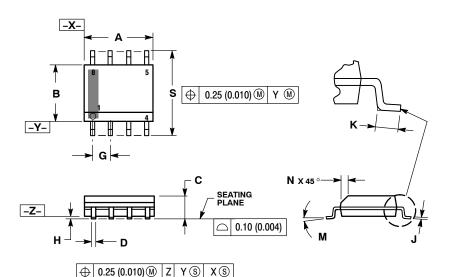
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DESCRIPTION:	SOT-223 (TO-261)		PAGE 2 OF 2	

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SOIC-8 NB CASE 751-07 **ISSUE AK**

DATE 16 FEB 2011



- NOTES:
 1. DIMENSIONING AND TOLERANCING PER
- ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: MILLIMETER.
- DIMENSION A AND B DO NOT INCLUDE MOLD PROTRUSION.
- MAXIMUM MOLD PROTRUSION 0.15 (0.006) PER SIDE
- DIMENSION D DOES NOT INCLUDE DAMBAR PROTRUSION. ALLOWABLE DAMBAR PROTRUSION SHALL BE 0.127 (0.005) TOTAL IN EXCESS OF THE D DIMENSION AT MAXIMUM MATERIAL CONDITION.
- 751-01 THRU 751-06 ARE OBSOLETE. NEW STANDARD IS 751-07.

	MILLIMETERS		INC	HES
DIM	MIN	MAX	MIN	MAX
Α	4.80	5.00	0.189	0.197
В	3.80	4.00	0.150	0.157
С	1.35	1.75	0.053	0.069
D	0.33	0.51	0.013	0.020
G	1.27	7 BSC	0.050 BSC	
Н	0.10	0.25	0.004	0.010
J	0.19	0.25	0.007	0.010
K	0.40	1.27	0.016	0.050
М	0 °	8 °	0 °	8 °
N	0.25	0.50	0.010	0.020
S	5.80	6.20	0.228	0.244

SOLDERING FOOTPRINT*



^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

GENERIC MARKING DIAGRAM*



XXXXX = Specific Device Code = Assembly Location = Wafer Lot

= Year = Work Week = Pb-Free Package XXXXXX AYWW AYWW H \mathbb{H} Discrete **Discrete** (Pb-Free)

XXXXXX = Specific Device Code = Assembly Location Α

= Year ww = Work Week

= Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.

STYLES ON PAGE 2

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SOIC-8 NB CASE 751-07 ISSUE AK

DATE 16 FEB 2011

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STYLE 1: PIN 1. EMITTER 2. COLLECTOR 3. COLLECTOR 4. EMITTER 5. EMITTER 6. BASE 7. BASE 8. EMITTER	STYLE 2: PIN 1. COLLECTOR, DIE, #1 2. COLLECTOR, #1 3. COLLECTOR, #2 4. COLLECTOR, #2 5. BASE, #2 6. EMITTER, #2 7. BASE, #1 8. EMITTER, #1	STYLE 3: PIN 1. DRAIN, DIE #1 2. DRAIN, #1 3. DRAIN, #2 4. DRAIN, #2 5. GATE, #2 6. SOURCE, #2 7. GATE, #1 8. SOURCE, #1	
STYLE 5: PIN 1. DRAIN 2. DRAIN 3. DRAIN 4. DRAIN 5. GATE 6. GATE 7. SOURCE 8. SOURCE	STYLE 6: PIN 1. SOURCE 2. DRAIN 3. DRAIN 4. SOURCE 5. SOURCE 6. GATE 7. GATE 8. SOURCE	STYLE 7: PIN 1. INPUT 2. EXTERNAL BYPASS 3. THIRD STAGE SOURCE 4. GROUND 5. DRAIN 6. GATE 3 7. SECOND STAGE Vd 8. FIRST STAGE Vd	STYLE 8: PIN 1. COLLECTOR, DIE #1 2. BASE, #1 3. BASE, #2 4. COLLECTOR, #2 5. COLLECTOR, #2 6. EMITTER, #2 7. EMITTER, #1 8. COLLECTOR, #1
STYLE 9: PIN 1. EMITTER, COMMON 2. COLLECTOR, DIE #1 3. COLLECTOR, DIE #2 4. EMITTER, COMMON 5. EMITTER, COMMON 6. BASE, DIE #2 7. BASE, DIE #1 8. EMITTER, COMMON	STYLE 10: PIN 1. GROUND 2. BIAS 1 3. OUTPUT 4. GROUND 5. GROUND 6. BIAS 2 7. INPUT 8. GROUND STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE	STYLE 11: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. DRAIN 2 7. DRAIN 1 8. DRAIN 1	STYLE 12: PIN 1. SOURCE 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
STYLE 13: PIN 1. N.C. 2. SOURCE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN	STYLE 14: PIN 1. N-SOURCE 2. N-GATE 3. P-SOURCE 4. P-GATE 5. P-DRAIN 6. P-DRAIN 7. N-DRAIN 8. N-DRAIN	8. DHAIN 1 STYLE 15: PIN 1. ANODE 1 2. ANODE 1 3. ANODE 1 4. ANODE 1 5. CATHODE, COMMON 6. CATHODE, COMMON 7. CATHODE, COMMON 8. CATHODE, COMMON	STYLE 16: PIN 1. EMITTER, DIE #1 2. BASE, DIE #1 3. EMITTER, DIE #2 4. BASE, DIE #2 5. COLLECTOR, DIE #2 6. COLLECTOR, DIE #2 7. COLLECTOR, DIE #1 8. COLLECTOR, DIE #1
STYLE 17: PIN 1. VCC 2. V2OUT 3. V1OUT 4. TXE 5. RXE 6. VEE 7. GND 8. ACC	STYLE 18: PIN 1. ANODE 2. ANODE 3. SOURCE 4. GATE 5. DRAIN 6. DRAIN 7. CATHODE 8. CATHODE	STYLE 19: PIN 1. SOURCE 1 2. GATE 1 3. SOURCE 2 4. GATE 2 5. DRAIN 2 6. MIRROR 2 7. DRAIN 1 8. MIRROR 1	STYLE 20: PIN 1. SOURCE (N) 2. GATE (N) 3. SOURCE (P) 4. GATE (P) 5. DRAIN 6. DRAIN 7. DRAIN 8. DRAIN
6. VEE 7. GND 8. ACC STYLE 21: PIN 1. CATHODE 1 2. CATHODE 2 3. CATHODE 3 4. CATHODE 4 5. CATHODE 5 6. COMMON ANODE 7. COMMON ANODE 8. CATHODE 6	STYLE 22: PIN 1. I/O LINE 1 2. COMMON CATHODE/VCC 3. COMMON CATHODE/VCC 4. I/O LINE 3 5. COMMON ANODE/GND 6. I/O LINE 4 7. I/O LINE 5 8. COMMON ANODE/GND	STYLE 23: PIN 1. LINE 1 IN 2. COMMON ANODE/GND 3. COMMON ANODE/GND 4. LINE 2 IN 5. LINE 2 OUT 6. COMMON ANODE/GND 7. COMMON ANODE/GND 8. LINE 1 OUT	a COLLECTOR/ANODE
STYLE 25: PIN 1. VIN 2. N/C 3. REXT 4. GND 5. IOUT 6. IOUT 7. IOUT 8. IOUT	STYLE 26: PIN 1. GND 2. dv/dt 3. ENABLE 4. ILIMIT 5. SOURCE 6. SOURCE 7. SOURCE 8. VCC	STYLE 27: PIN 1. ILIMIT 2. OVLO 3. UVLO 4. INPUT+ 5. SOURCE 6. SOURCE 7. SOURCE 8. DRAIN	STYLE 28: PIN 1. SW_TO_GND 2. DASIC_OFF 3. DASIC_SW_DET 4. GND 5. V_MON 6. VBULK 7. VBULK 8. VIN
STYLE 29: PIN 1. BASE, DIE #1 2. EMITTER, #1 3. BASE, #2 4. EMITTER, #2 5. COLLECTOR, #2 6. COLLECTOR, #2 7. COLLECTOR, #1 8. COLLECTOR, #1	STYLE 30: PIN 1. DRAIN 1 2. DRAIN 1 3. GATE 2 4. SOURCE 2 5. SOURCE 1/DRAIN 2 6. SOURCE 1/DRAIN 2 7. SOURCE 1/DRAIN 2 8. GATE 1		

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